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### Features

- International standard package
- High Surge Capability
- Simple Mounting

### Internal Circuit

### Blocking - Off State

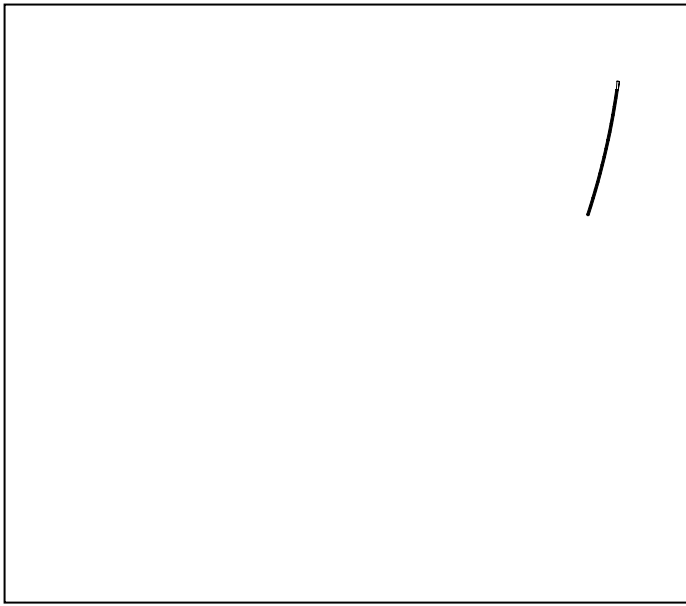
TYPE		V <sub>DRM</sub> /V <sub>RRM</sub>	V <sub>DSM</sub> /V <sub>RSM</sub>	Units
MT330C(A/K)12T3	MT330C(A/K)B12T3	1200	1400	V
MT330C(A/K)14T3	MT330C(A/K)B14T3	1400	1600	V
MT330C(A/K)16T3	MT330C(A/K)B16T3	1600	1800	V
MT330C(A/K)18T3	MT330C(A/K)B18T3	1800	2000	V

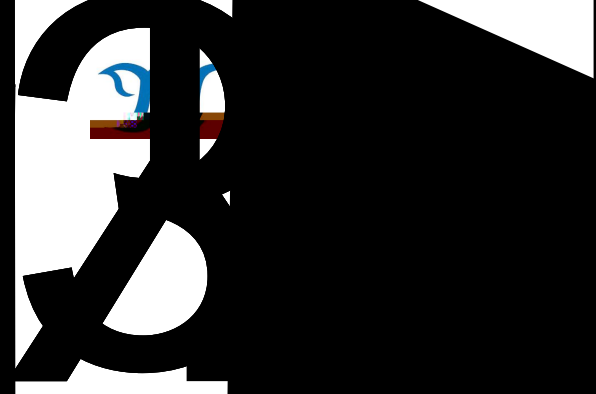
### Maximum Ratings

Symbol	Conditions	Values	Units
I <sub>TAV</sub>	Sine 180°;T <sub>c</sub> =85	330	A
I <sub>TSM</sub>	T <sub>VJ</sub> =125 t=10ms, sine	9100	A
I <sup>2</sup> t	T <sub>VJ</sub> =125 t=10ms, sine	414050	A <sup>2</sup> s
Visol	a.c.50HZ;r.m.s.;1min,I <sub>iso</sub> :2mA(MAX)	2500	V
T <sub>vj</sub>		-40 to 125	
T <sub>stg</sub>		-40 to 125	
M <sub>t</sub>	To terminals(M8)	12±15%	Nm
M <sub>s</sub>	To heatsink(M6)	6±15%	Nm
di/dt	T <sub>VJ</sub> = T <sub>VJM</sub> ,V <sub>DM</sub> 2/3V <sub>DRM</sub> I <sub>GM</sub> =1.5A t <sub>r</sub> 0.5μs	100	A/μs
dv/dt	T <sub>VJ</sub> = T <sub>VJM</sub> ,2/3V <sub>DRM</sub> , linear voltage rise	1000	V/μs
Weight	Module(Approximately)	690	g

### Thermal Characteristics

Symbol	Conditions	Values	Units
R <sub>th(j-c)</sub>	per chip	0.097	/W
R <sub>th(c-</sub>			





M50-T00-2012

Yangzhou